

# PNP general purpose double transistor

# PUMT1

### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V)
- Reduces number of components and boardspace.

### APPLICATIONS

- General purpose switching and amplification.

### DESCRIPTION

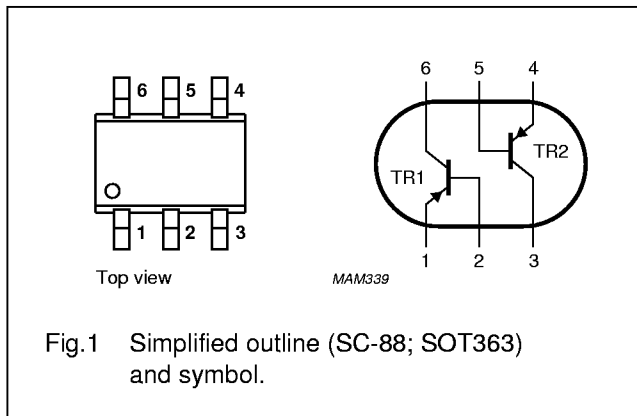
Two independently operating PNP transistors in an SC-88; SOT363 plastic package. NPN complement: PUMX1.

### MARKING

TYPE NUMBER	MARKING CODE
PUMT1	FtF

### PINNING

PIN	DESCRIPTION
1, 4	emitter TR1; TR2
2, 5	base TR1; TR2
3, 6	collector TR2; TR1



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor</b>					
V <sub>CBO</sub>	collector-base voltage	open emitter	–	–50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	–40	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	–5	V
I <sub>C</sub>	collector current (DC)		–	–100	mA
I <sub>CM</sub>	peak collector current		–	–200	mA
I <sub>BM</sub>	peak base current		–	–200	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	–	200	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C
<b>Per device</b>					
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C; note 1	–	300	mW

### Note

1. Device mounted on an FR4 printed-circuit board.

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
<b>Per device</b>				
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	416	K/W

**Note**

1. Device mounted on an FR4 printed-circuit board.

## CHARACTERISTICS

$T_{amb} = 25\text{ °C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
<b>Per transistor</b>					
$I_{CBO}$	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–100	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ °C}$	–	–10	$\mu\text{A}$
$I_{EBO}$	emitter cut-off current	$I_C = 0; V_{EB} = -4\text{ V}$	–	–100	nA
$h_{FE}$	DC current gain	$I_C = -1\text{ mA}; V_{CE} = -6\text{ V}$	120	–	
$V_{CEsat}$	collector-emitter saturation voltage	$I_C = -50\text{ mA}; I_B = -5\text{ mA}; \text{note 1}$	–	–200	mV
$C_c$	collector capacitance	$I_E = i_e = 0; V_{CB} = -12\text{ V}; f = 1\text{ MHz}$	–	2.2	pF
$f_T$	transition frequency	$I_C = -2\text{ mA}; V_{CE} = -12\text{ V}; f = 100\text{ MHz}$	100	–	MHz

**Note**

1. Pulse test:  $t_p \leq 300\ \mu\text{s}$ ;  $\delta \leq 0.02$ .

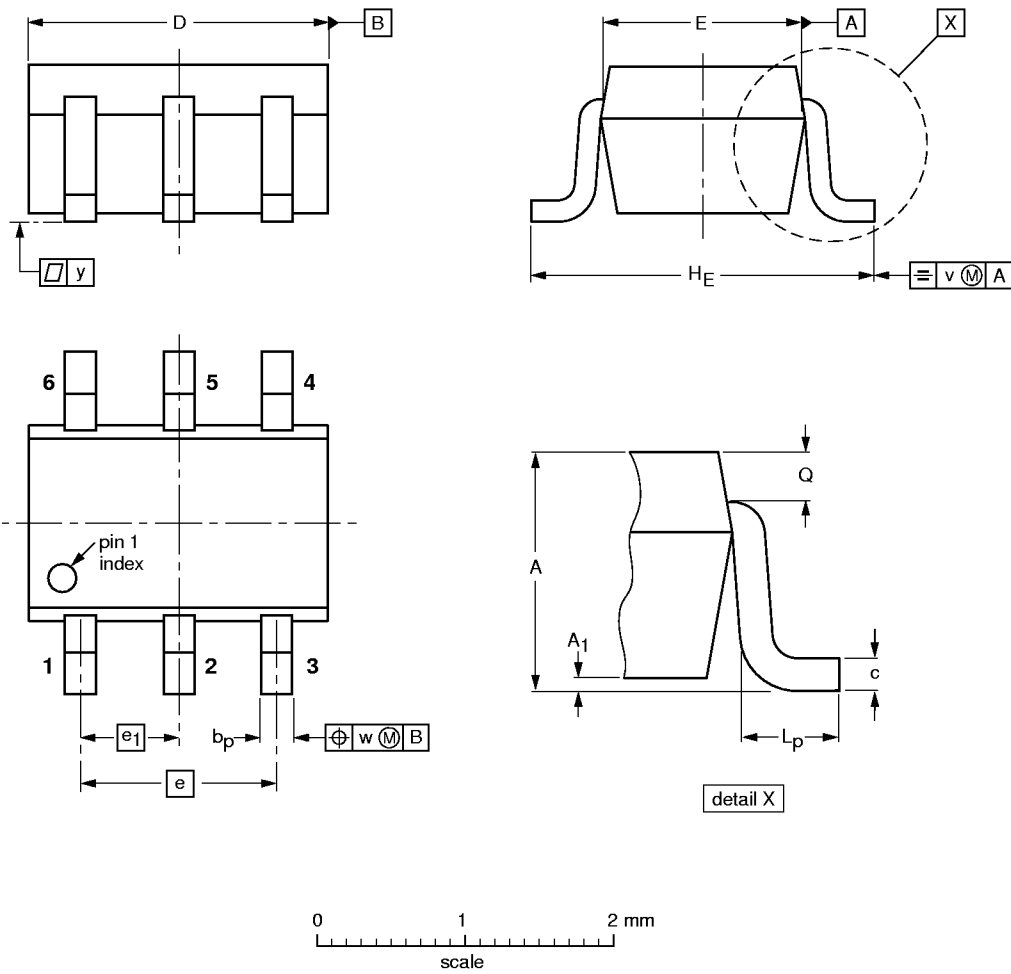
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT363



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT363			SC-88			97-02-28